

Features

- High Linear Gain: 33 dB Typical
- High Saturated Output Power: +33 dBm Typ.
- High Power Added Efficiency: 25% Typ.
- 50 Ω Input / Output Broadband Matched
- Integrated Output Power Detector

Description

M/A-COM's AM42-0039 is a three stage MMIC power amplifier in a bolt down ceramic package, allowing easy assembly. The AM42-0039 employs a fully matched chip with internally decoupled gate and drain bias networks. The AM42-0039 is designed to operate from a constant current drain supply or a constant voltage gate supply. By varying the bias conditions, the saturated output power performance of this device may be tailored for various applications.

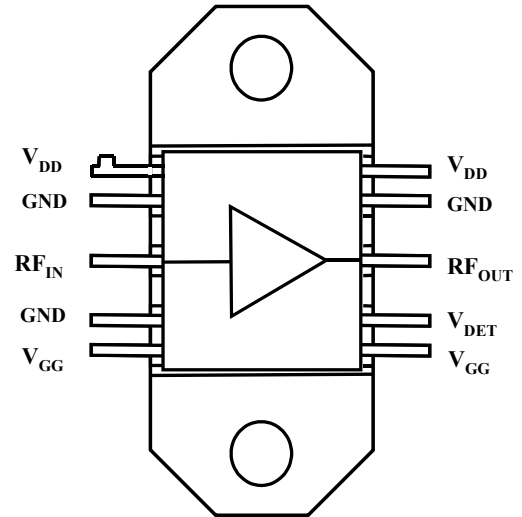
The AM42-0039 is ideally suited for use as an output stage or a driver amplifier in VSAT systems. The AM42-0039 includes internal supply line bypassing in the package, minimizing the number of external components required. M/A-COM's AM42-0039 is fabricated using a mature 0.5 micron MBE based GaAs MESFET process. The process features full passivation for increased performance and reliability. This product is 100% RF tested to ensure compliance to performance specifications.

Absolute Maximum Ratings^{1,2}

| Parameter | Absolute Maximum |
|-----------------------|---|
| Input Power | +15 dBm |
| Operating Voltages | $V_{DD} = +10$ volts; $V_{GG} = -3$ volts; $V_{DD} - V_{GG} = 12$ volts |
| I_{ds} | 1200 mA |
| Channel Temperature | +150 °C |
| Operating Temperature | -40 °C to +80 °C |
| Storage Temperature | -65 °C to +150 °C |

1. Exceeding any one or a combination of these limits may cause permanent damage.
2. Adequate heat sinking and grounding required on flange base.

Functional Schematic



Pin Configuration

| PIN No. | PIN Name | Description |
|---------|------------|-----------------------|
| 1 | V_{DD} | Drain Supply |
| 2 | GND | DC and RF Ground |
| 3 | RF_{IN} | RF Input |
| 4 | GND | DC and RF Ground |
| 5 | V_{GG} | Gate Supply |
| 6 | V_{GG} | Gate Supply |
| 7 | V_{DET} | Output Power Detector |
| 8 | RF_{OUT} | RF Output |
| 9 | GND | DC and RF Ground |
| 10 | V_{DD} | Drain Supply |
| Flange | GND | DC and RF Ground |

Ordering Information

| Part Number | Package |
|-------------|--------------------------------|
| AM42-0039 | CR15 Ceramic Bolt Down Package |

- **North America:** Tel. (800) 366-2266
- **Asia/Pacific:** Tel. +81-44-844-8296, Fax +81-44-844-8298
- **Europe:** Tel. +44 (1908) 574 200, Fax +44 (1908) 574 300

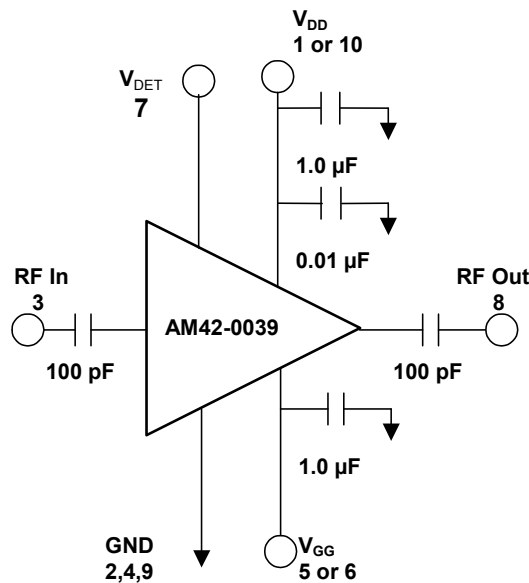
M/A-COM Inc. and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.

Visit www.macom.com for additional data sheets and product information.

Electrical Specifications:

| Parameter | Test Conditions | Units | Min. | Typ. | Max. |
|---------------------------------------|---|-------|------|-------|-------|
| Linear Gain | Pin = -10 dBm | dB | 31 | 33 | 35 |
| Input VSWR | Pin = -10 dBm | | | 2.5:1 | 3.0:1 |
| Output VSWR | Pin = -10 dBm | | | 2.5:1 | |
| Output Power | Pin = +3 dBm, I _{ds} = 900 mA Typ. | dBm | 31.7 | 33.0 | |
| Output Power vs. Frequency | Pin = +3 dBm, I _{ds} = 900 mA Typ. (5.9 to 6.4 GHz) | dB | | ±0.3 | ±0.75 |
| | Pin = +3 dBm, I _{ds} = 900 mA Typ. (6.4 to 7.1 GHz) | dB | | ±0.3 | ±0.75 |
| Output Power vs. Temperature | T _A = -40°C to +85°C, Pin = +7 dBm | dB | | ±0.4 | |
| Drain Bias Current | Pin = +3 dBm | mA | 800 | 900 | 1000 |
| Gate Bias Voltage | Pin = +3 dBm, I _{ds} = 900 mA Typ. | V | -2.0 | -1.2 | -0.4 |
| Gate Bias Current | Pin = +3 dBm, I _{ds} = 900 mA Typ. | mA | | 10 | 20 |
| Thermal Resistance (θ _{JC}) | 25°C Heat Sink | °C/W | | 7.0 | |
| Second Harmonic | Pin = +3 dBm, I _{ds} = 900 mA Typ. | dBc | | -35 | |
| Third Harmonic | Pin = +3 dBm, I _{ds} = 900 mA Typ. | dBc | | -45 | |
| Detector Voltage | Pin = +3 dBm, I _{ds} = 900 mA Typ. | V | | 4.0 | |

Application Schematic ^{3,4,5}



3. Apply -2 volts to pin 5 or 6 (V_{GG}), prior to applying +8 volts to pins 1 or 10 (V_{DD}). Adjust V_{GG} for typical drain current.
4. External DC blocking capacitors required on the RF ports.
5. For optimum IP3 performance, V_{DD} bypass capacitors should be placed within 0.5 inches of the V_{DD} leads.

Handling Procedures

Please observe the following precautions to avoid damage to the AM42-0039:

Static Sensitivity

Gallium arsenide integrated circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Use proper ESD precautions when handling these devices.

Operating the AM42-0039

The AM42-0039 is static sensitive. Please handle with care. To operate the device, follow these steps.

1. Apply -2.5 Volts to V_{GG}.
2. Ramp V_{DD} to +8V.
3. Adjust V_{GG} to set quiescent drain current .
4. Apply RF.
5. Power down sequence in reverse. Turn gate voltage off last.

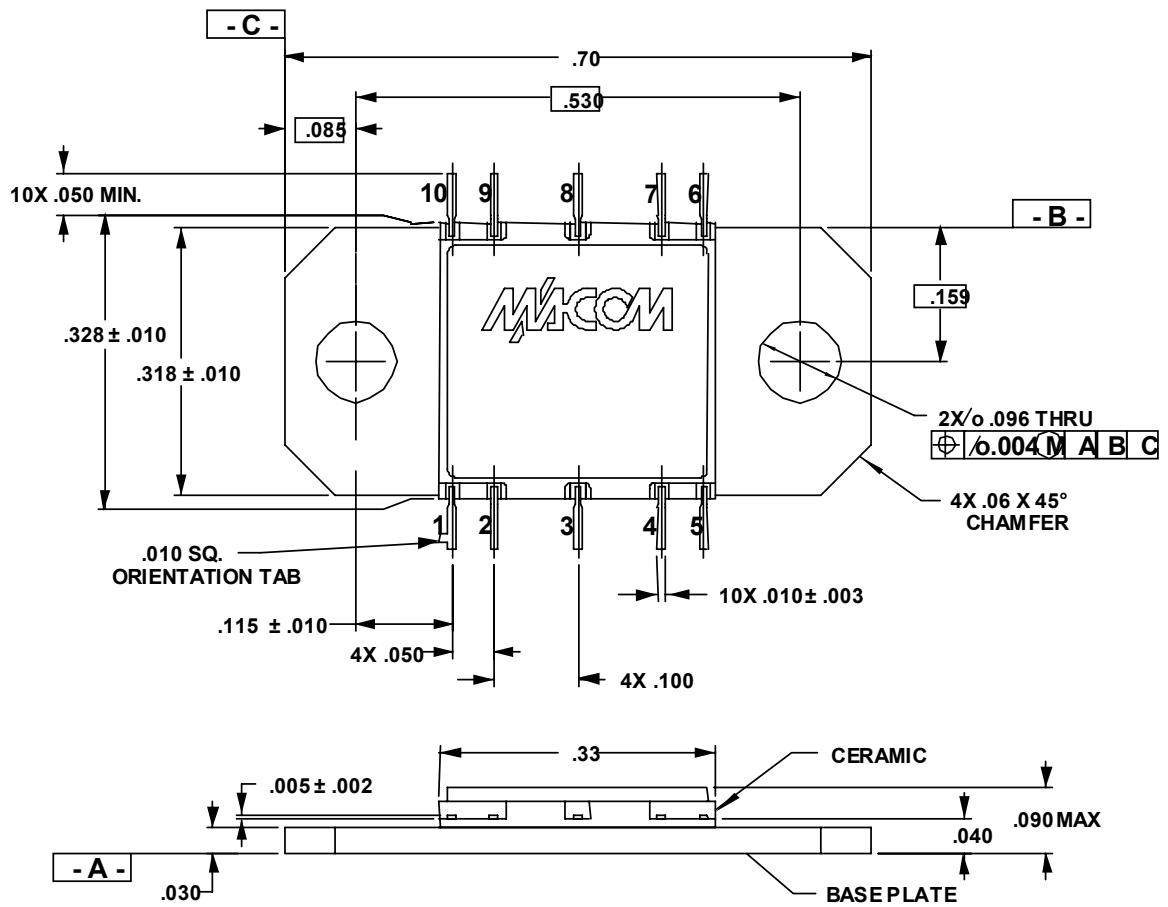
M/A-COM Inc. and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.

Visit www.macom.com for additional data sheets and product information.

- North America: Tel. (800) 366-2266
- Asia/Pacific: Tel. +81-44-844-8296, Fax +81-44-844-8298
- Europe: Tel. +44 (1908) 574 200, Fax +44 (1908) 574 300

CR-15

V1A



M/A-COM Inc. and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.

Visit www.macom.com for additional data sheets and product information.

- North America: Tel. (800) 366-2266
- Asia/Pacific: Tel. +81-44-844-8296, Fax +81-44-844-8298
- Europe: Tel. +44 (1908) 574 200, Fax +44 (1908) 574 300